Electronic Supplementary Material (ESI) for Nanoscale Advances.
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Supplementary Information: Enhancing Light Emission of GaAs Nanowires by Pressure-Modulated Charge Transfer

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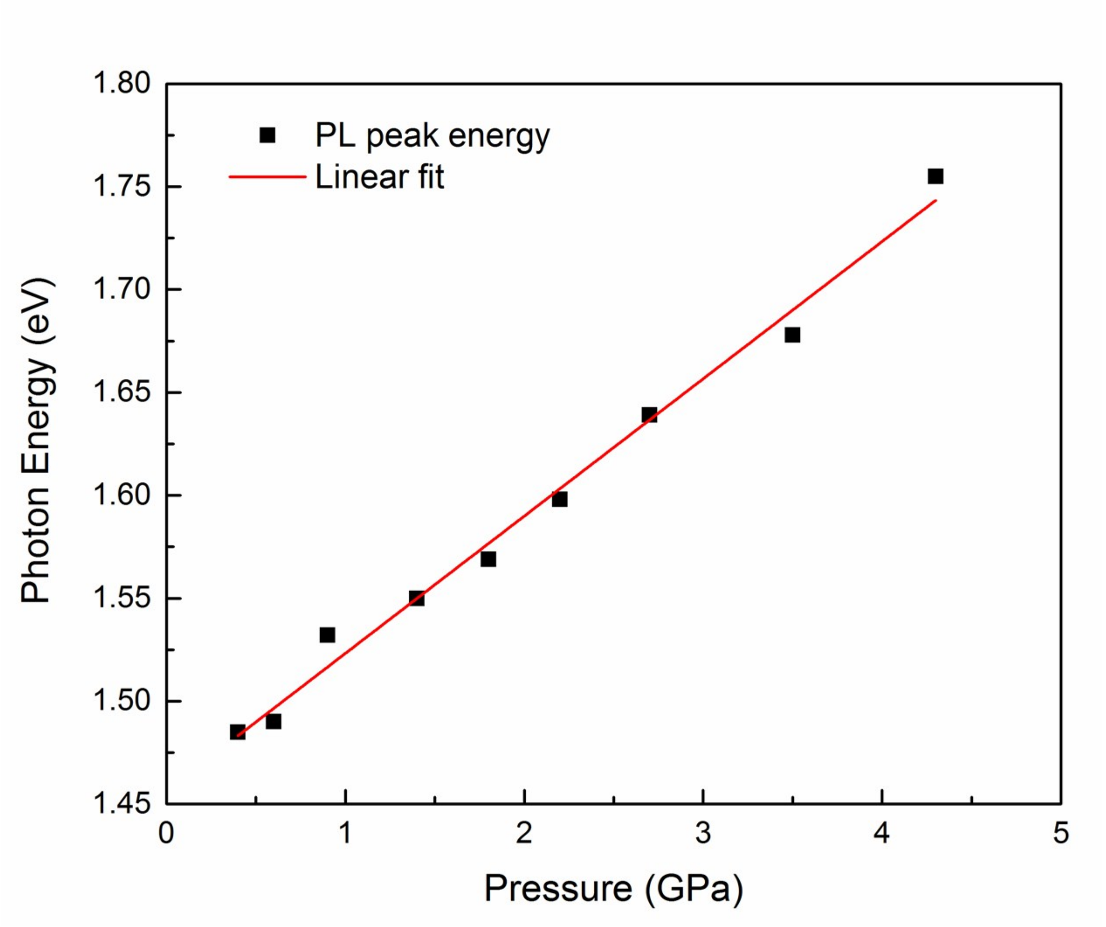

Fig. S1 Peak energy evolution of PL peaks in GaAs nanowires with no PTM fitting as a function of pressure upon compression from 0.4 GPa to 4.2 GPa.

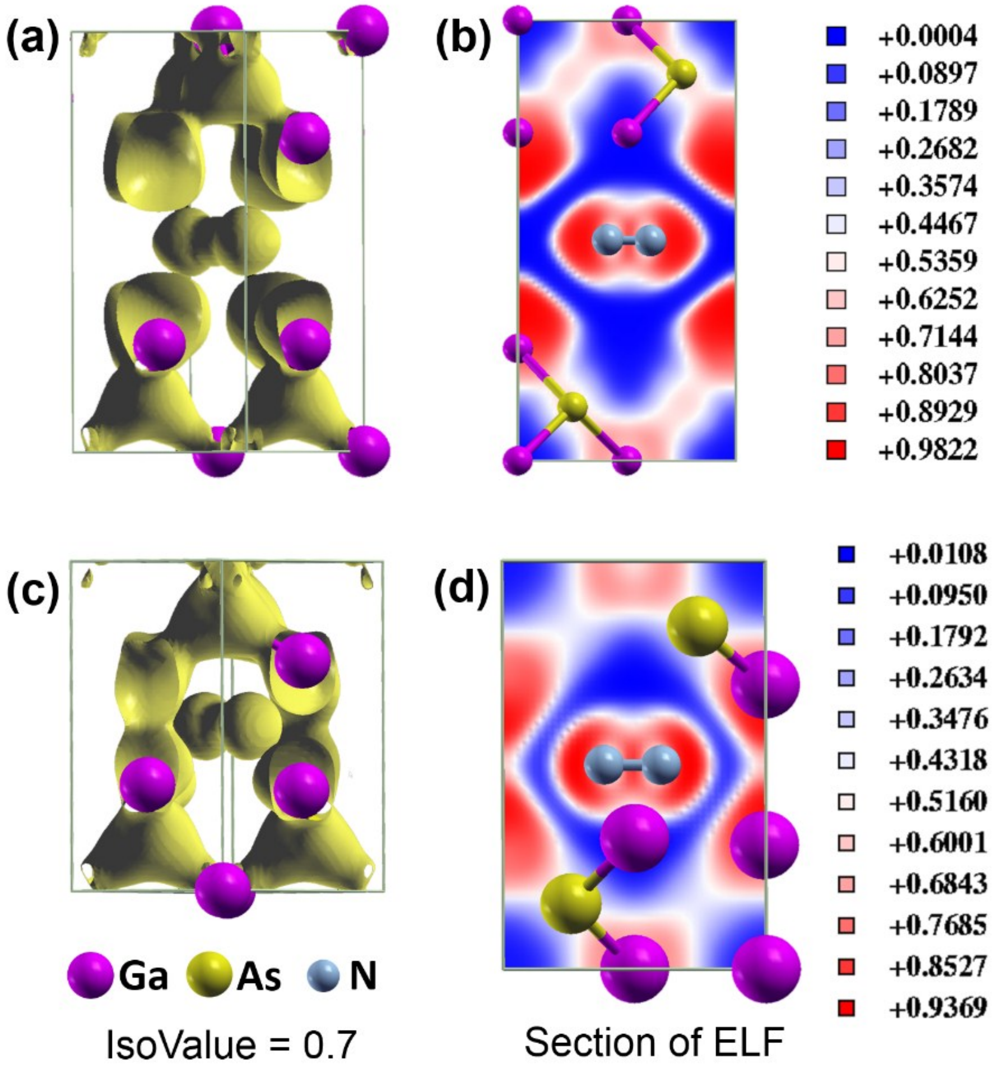

Fig. S2 ELF of the N_2@GaAs at (a) 0 GPa and correspond section (b), (c) 3 GPa and corresponding section (d). The IsoValue of ELF section is 0.7.